

# 2SB0936 (2SB936), 2SB0936A (2SB936A)

## Silicon PNP epitaxial planar type

For low-voltage switching

### ■ Features

- Low collector-emitter saturation voltage  $V_{CE(sat)}$
- High-speed switching
- N type package enabling direct soldering of the radiating fin to the printed circuit board, etc. of small electronic equipment.

### ■ Absolute Maximum Ratings $T_C = 25^\circ\text{C}$

| Parameter                                | Symbol    | Rating                   | Unit             |   |
|--|-----------|--------------------------|------------------|---|
| Collector-base voltage<br>(Emitter open) | 2SB0936   | $V_{CBO}$                | -40              | V |
|  | 2SB0936A  |                          | -50              |   |
| Collector-emitter voltage<br>(Base open) | 2SB0936   | $V_{CEO}$                | -20              | V |
|  | 2SB0936A  |                          | -40              |   |
| Emitter-base voltage (Collector open)    | $V_{EBO}$ | -5                       | V                |   |
| Collector current                        | $I_C$     | -10                      | A                |   |
| Peak collector current                   | $I_{CP}$  | -20                      | A                |   |
| Collector power dissipation              | $P_C$     |                          | 40               | W |
|  |           | $T_a = 25^\circ\text{C}$ | 1.3              |   |
| Junction temperature                     | $T_j$     | 150                      | $^\circ\text{C}$ |   |
| Storage temperature                      | $T_{stg}$ | -55 to +150              | $^\circ\text{C}$ |   |

### ■ Electrical Characteristics $T_C = 25^\circ\text{C} \pm 3^\circ\text{C}$

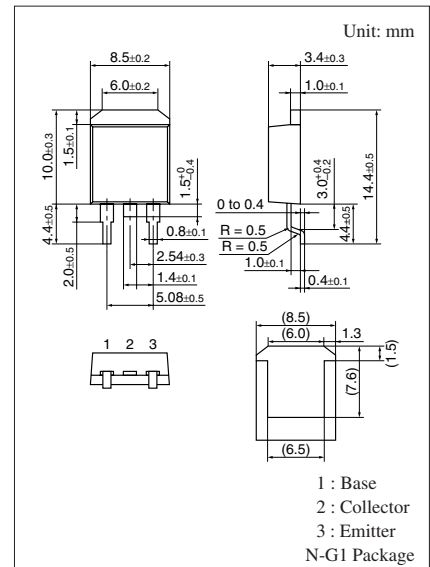
| Parameter   | Symbol        | Conditions  | Min | Typ | Max  | Unit          |
|---|---------------|---|-----|-----|------|---------------|
| Collector-emitter voltage<br>(Base open)                            | $V_{CEO}$     | $I_C = -10\text{ mA}, I_B = 0$                                  | -20 |     |      | V             |
|   |               |   | -40 |     |      |               |
| Collector-base cutoff<br>current (Emitter open)                     | $I_{CBO}$     | $V_{CB} = -40\text{ V}, I_E = 0$                                |     |     | -50  | $\mu\text{A}$ |
|   |               | $V_{CB} = -50\text{ V}, I_E = 0$                                |     |     | -50  |               |
| Emitter-base cutoff current (Collector open)                        | $I_{EBO}$     | $V_{EB} = -5\text{ V}, I_C = 0$                                 |     |     | -50  | $\mu\text{A}$ |
| Forward current transfer ratio                                      | $h_{FE1}^*$   | $V_{CE} = -2\text{ V}, I_C = -0.1\text{ A}$                     | 45  |     |      | —             |
|   | $h_{FE2}$     | $V_{CE} = -2\text{ V}, I_C = -3\text{ A}$                       | 90  | 260 |      |               |
| Base-emitter voltage  | $V_{BE(sat)}$ | $I_C = -10\text{ A}, I_B = -0.33\text{ A}$                      |     |     | -1.5 | V             |
| Collector-emitter saturation voltage                                | $V_{CE(sat)}$ | $I_C = -10\text{ A}, I_B = -0.33\text{ A}$                      |     |     | -0.6 | V             |
| Transition frequency  | $f_T$         | $V_{CE} = -10\text{ V}, I_C = -0.5\text{ A}, f = 10\text{ MHz}$ |     | 100 |      | MHz           |
| Collector output capacitance<br>(Common base, input open circuited) | $C_{ob}$      | $V_{CB} = -10\text{ V}, I_E = 0, f = 1\text{ MHz}$              |     | 400 |      | pF            |
| Turn-on time  | $t_{on}$      | $I_C = -3\text{ A},$  |     | 0.1 |      | $\mu\text{s}$ |
| Storage time  | $t_{stg}$     | $I_{B1} = -0.1\text{ A}, I_{B2} = 0.1\text{ A}$                 |     | 0.5 |      |               |
| Fall time   | $t_f$         | $V_{CC} = -20\text{ V}$   |     | 0.1 |      |               |

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

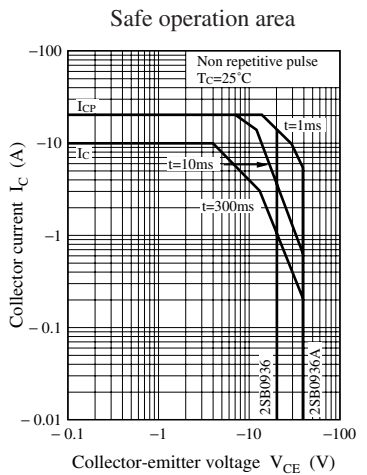
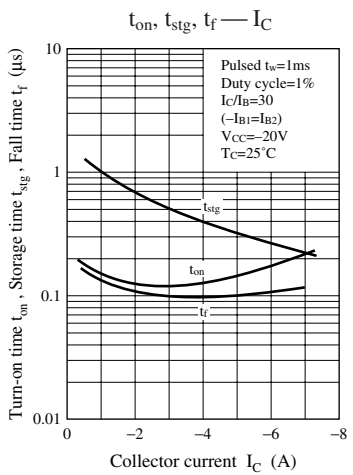
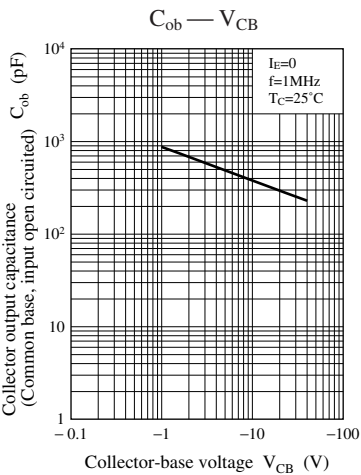
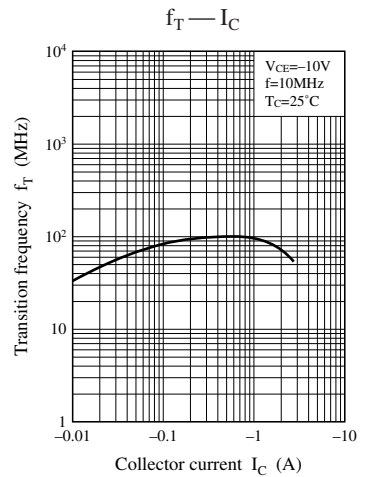
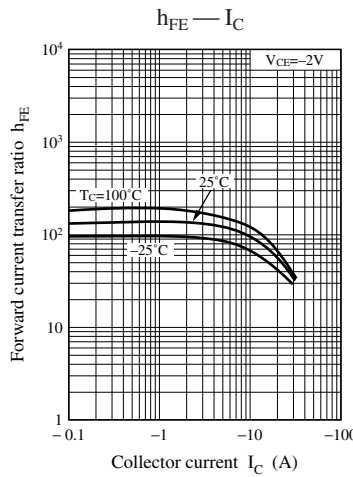
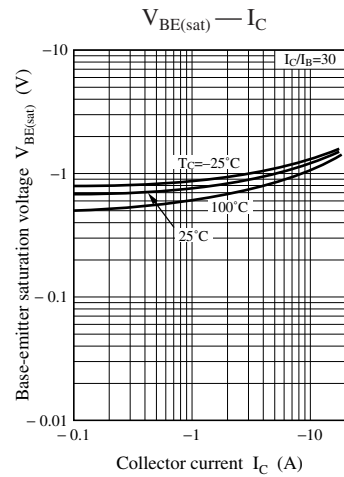
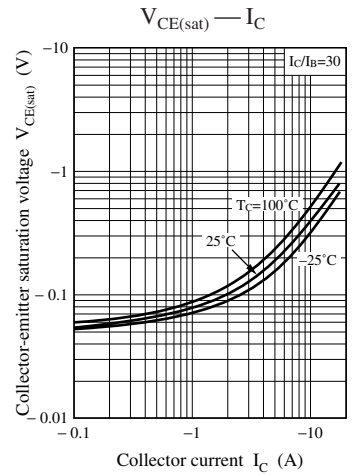
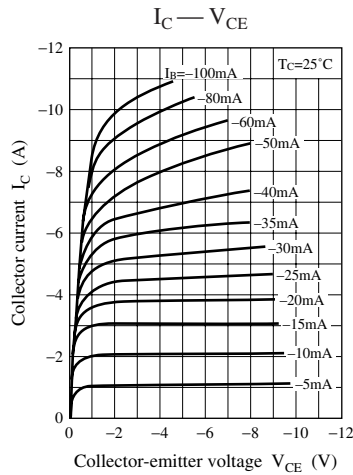
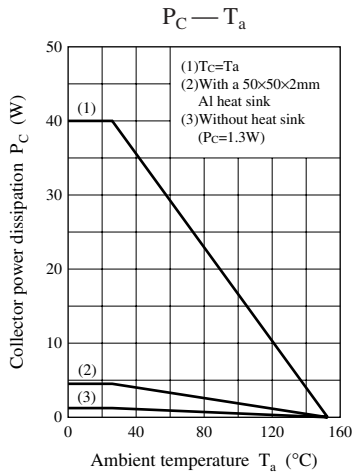
2. \*: Rank classification

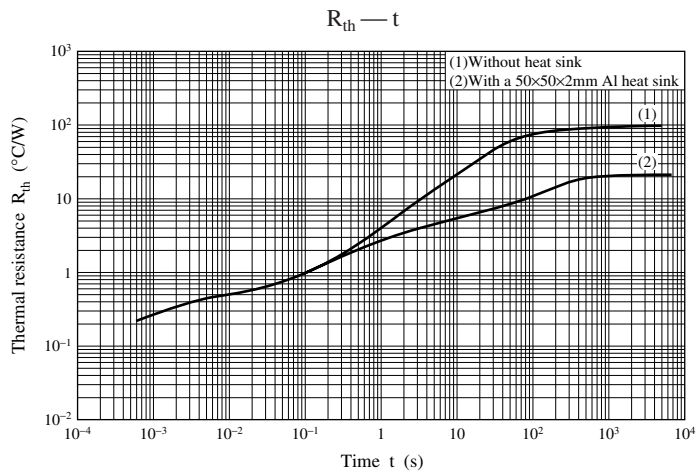
| Rank      | Q         | P          |
|-----------|-----------|------------|
| $h_{FE1}$ | 90 to 180 | 130 to 260 |

Note) The part number in the parenthesis shows conventional part number.



Note) Self-supported type package is also prepared.





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